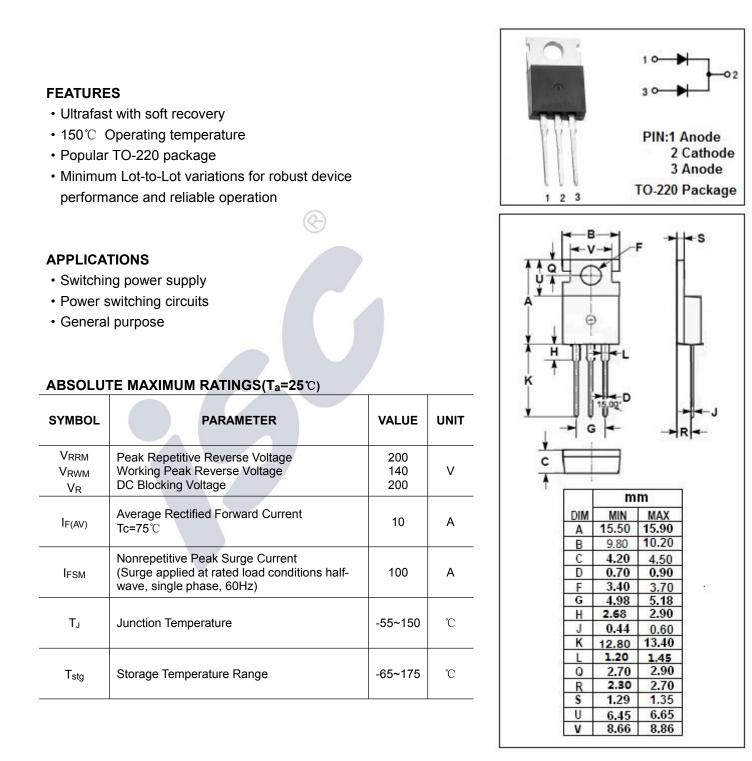


INCHANGE SEMICONDUCTOR

SF1020CT





INCHANGE SEMICONDUCTOR

Ultra fast Rectifier

SF1020CT

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	2.5	°C/W

ELECTRICAL CHARACTERISTICS(Ta=25°C) (Pulse Test: Pulse Width=300 µ s,Duty Cycle≤2%)

SYMBOL	PARAMETER	CONDITIONS	МАХ	UNIT
V _{F*}	Maximum Instantaneous Forward Voltage	I _F =5A ;Tj=25℃	0.98	V
I _{R*}	Maximum Instantaneous Reverse Current	V _R = V _{RWM} ;Tj=25℃ V _R = V _{RWM} ;Tj=125℃	5 250	μA
trr	Maximum Reverse Recovery Time	I _F =0.5A;I _R =1A;I _{RR} =0.25A	35	ns

*:Pulse test ,Pulse width=300us,duty cycle≤2%

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